

Index

- AC analysis, 69
- ACM (advanced compact model), 28
- active load, 94
- amplifier
 - charge, 18, 200
 - common-source, 93
 - differential, 159, 179
 - folded-cascode, 18
 - low-noise (LNA), 18, 188
 - two-stage, 18, 184
- backgate parameter, 22
- balun
 - active, 188
- bias
 - cascode, 175
 - constant current, 215f. 5.35
 - constant transconductance, 215, 221
- bias circuit
 - constant transconductance, 165
- bias voltage, 62
- bipolar junction transistor (BJT), 27
- BSIM (Berkeley short-channel IGFET model), 2, 39
- bulk potential, 23
- Cadence Spectre, 39, 303
- capacitance
 - extrinsic, 69, 90
 - gate-to-bulk, 57
 - gate-to-drain, 56
 - gate-to-source, 56
 - junction, 56, 62, 90
- cds_srr, 304
- channel length modulation, 40, 49, 295
- charge redistribution, 226
- charge sheet model, 17, 21
- class-A, 5
- CMFB (common-mode feedback), 227f. 6.2, 240
- CMOS (complementary metal-oxide-semiconductor), 1
- common mode, 282
- common-gate stage, 189
- common-mode feedback, 105
- common-source stage, 189
- compliance voltage, 173
- configuration file, 305
- contour plots, 85f. 3.18
- corner frequency, 63, 229
- current density, 11, 44, 83
- current factor, 22, 29, 151
- current mirror, 153, 171
- current-mirror load, 108
- DC sweep, 9, 303
- de-normalization, 66, 96
- depletion region, 41
- DIBL (drain-induced barrier lowering), 17, 40, 48, 68, 74, 80, 106, 146, 295
- differential pair, 5, 13, 62, 102, 131
- diffusion, 21
- distortion, 15, 18, 71, 126
 - cancellation, 199
 - differential pair, 131
 - fractional harmonic, 129, 196
 - harmonic, 128, 141
 - intercept point, 199
 - null, 130, 144, 196
 - output conductance, 139
 - transconductance, 126
- drain current
 - normalized, 29
- drift, 21
- dynamic range, 95, 120
- Early voltage, 53, 68, 94, 173
- effective noise charge (ENC), 203
- EKV model (Enz Krummenacher Vittoz model), 5, 28
 - basic, 21, 28, 31, 127, 166, 292
- fan-out, 12, 64, 83, 116, 203, 230
- feedback
 - series-shunt, 180
 - shunt-shunt, 201
- feedback factor, 229
 - maximum possible, 229
- figure of merit, 6
- finger partitioning, 316

- finger width, 316
- flat-band voltage, 28
- full design automation, 3
- full design handcrafting, 3
- gain boosting, 265
- gain error
 - static, 230
- gate overdrive, 15
- gate overdrive voltage, 7
- GBW (gain-bandwidth product), 12, 64
- generic flow, 12
- Hooge model, 121
- IGS (intrinsic gain stage), 17, 62, 114
- interpolation, 307, 310
- interpolation method, 308
- intrinsic gain, 54, 63, 70, 217, 319
- inversion charge, 7
- inversion coefficient, 5, 15
- inversion level, 4
- iterative sizing, 92
- large-signal characteristic, 98, 102
- layout, 315
- layout area, 154, 181, 213
- layout dependent effects, 315
- line regulation, 186
- LNA (low-noise amplifier), 8
- load capacitance, 229
 - total, 229
- load regulation, 180
- lookup, 9, 39, 307
- lookup table, 3, 9, 39, 294, 304, 315
- lookupVGS, 67, 82 n.3, 106, 309
- loop gain, 228
 - low-frequency, 228, 253, 255
- McWorther model, 121
- Miller compensation, 267
- Miller effect, 111, 185
- Miller theorem, 65
- minimum width, 317
- mismatch, 18
 - current factor, 151
 - Pelgrom model, 152
 - random, 151
 - systematic, 151, 171
 - threshold voltage, 151
- mobile charge density, 22
 - normalized, 29, 33, 125
- mobility degradation, 1, 39, 42, 108, 118, 127, 141, 293
- moderate inversion, 1, 10, 24, 28, 43, 100, 236
- narrow-width effects, 67
- neutralization, 268
- noise, 18
 - active load, 119
 - cancellation, 189
 - electronic, 114
 - flicker, 114, 121
 - flicker corner, 121
 - input-referred, 116
 - man-made, 114
 - power spectral density, 230
 - scaling, 241
 - shot, 114
 - supply, 177, 178
 - thermal, 114
 - total integrated, 124, 230
- noise figure, 190, 192
- notation, 18
- offset drift, 160
- on-resistance, 286
- optimization
 - constant drain current, 205
 - constant noise and bandwidth, 207, 231
 - constant transit frequency, 204
- OTA (operational transconductance amplifier), 18, 226
 - basic, 226
 - folded-cascode, 249, 284
 - two-stage, 267, 284
- output conductance, 51
- overdesign, 222
- pinch-off voltage, 24, 30, 294
- pocket implants, 47, 152
- pole
 - dominant, 111, 184, 269
 - non-dominant, 111, 184, 249, 255, 269
- pole-zero doublet, 110
- power supply rejection (PSR), 179
- process corners, 47, 214, 299
- PSP (Penn State Philips model), 2, 17, 39, 58
- quasi-static model, 56, 65
- return ratio, 228
- reverse short channel effect, 47
- self-loading, 91, 96, 110, 253, 269
- sensitivity parameters, 51
- settling error
 - dynamic, 230
- settling time, 230, 244
- shallow trench isolation, 315
- silicon on insulator (SOI), 27
- slew rate, 243, 267, 281
- slewing, 242, 266, 281
 - asymmetric, 282
- slewing time, 244
- specific current, 16, 29, 44, 49, 108, 292

- Spectre Matlab Toolbox, 39, 304
square-law, 1, 6
square-law model, 33, 134
step response, 230
 critically damped, 251
strong inversion, 10, 23, 35, 45, 100, 236
subthreshold slope factor, 27, 108, 114, 292
surface potential, 21, 24
switch resistance, 226
switched-capacitor circuits, 226
- Taylor series, 126
 two-dimensional, 139
technology scaling, 125
temperature variations, 165
thermal voltage, 14, 22
threshold voltage, 23, 28, 31, 41, 47, 151, 292, 315
threshold voltage roll-off, 47
time constant, 230
transcapacitance, 56
transconductance, 34
 transconductance efficiency, 4, 27, 34, 65
 normalized, 34, 43
 transit frequency, 12, 57, 70, 73, 117, 217, 319
 transmission gate, 285
- unity gain frequency, 64
- V_{Dsat} , 7, 15, 26, 45, 52, 71, 94, 99, 174, 216
voltage biasing, 15
voltage regulator, 177
 low-dropout (LDO), 18, 108, 177
- weak inversion, 1, 10, 14, 23, 33, 34, 45, 65, 79, 83, 156,
 167, 233
weak inversion knee, 81
width independence, 9
- XTRACT, 36 n.6, 41, 47, 51, 294, 297
- zero
 right half-plane, 184, 229